

Features

- Low Capacitance Diode Array for ESD Protection in Four Data Lines
- SOT23-6 package
- Low Capacitance (1.5 pf Between I/O-I/O Lines)
- Low leakage current
- Protection one data/power line to:
- IEC 61000-4-2 $\pm 8\text{kV}$ contact $\pm 15\text{kV}$ air
- This is a Pb-Free Device



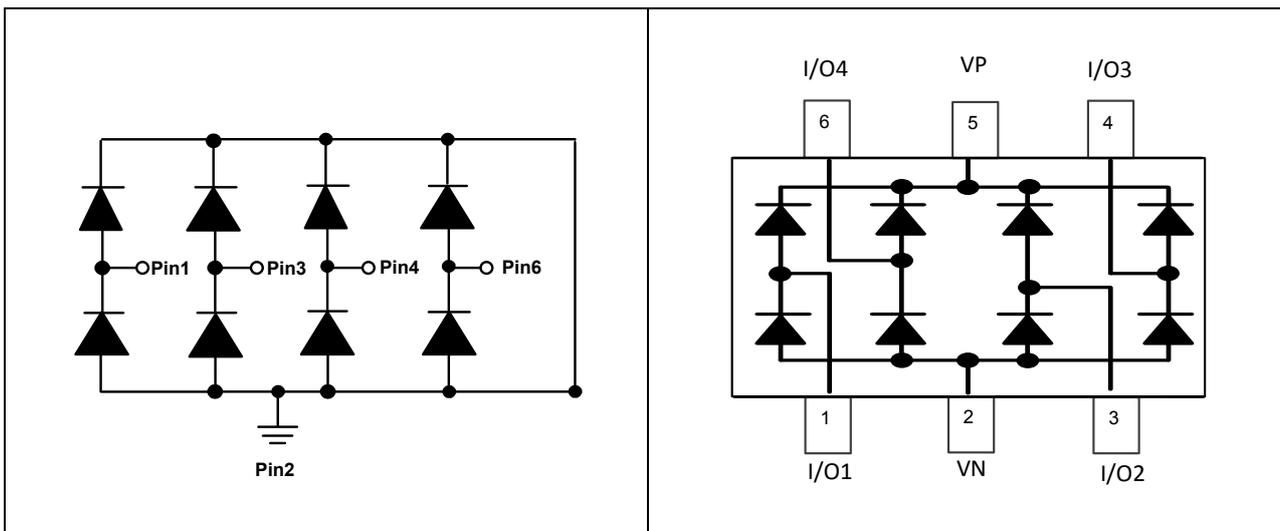
Applications

- USB 1.1 and 2.0 Data Line Protection
- HDSL, IDSL Secondary IC Protection
- Video Line Protection
- Microcontroller Input Protection

Mechanical Data

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Schematic & PIN Configuration



MAXIMUM RATINGS (Each Diode) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Peak Forward Surge Current	I_{FM}	500	mA
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-Repetitive Peak Forward Current $t = 1.0 \mu\text{s}$ $t = 1.0 \text{ms}$ $t = 1.0 \text{S}$	I_{FSM}	2.0 1.0 0.5	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Lead Solder Temperature, Maximum 10 Seconds Duration	T_L	260	$^\circ\text{C}$
Junction Temperature	T_J	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(BR)}$	70	-	-	V
Reverse Voltage Leakage Current ($V_R = 70 \text{Vdc}$) ($V_R = 25 \text{Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	-	-	2.5 30 50	μA
Capacitance (between I/O pins) ($V_R = 0 \text{V}$, $f = 1.0 \text{MHz}$)	C_D	-	-	1.5	pF
Capacitance (between I/O pin and ground) ($V_R = 0 \text{V}$, $f = 1.0 \text{MHz}$)	C_D	-	-	3	pF
Forward Voltage ($I_F = 1.0 \text{mAdc}$) ($I_F = 10 \text{mAdc}$) ($I_F = 50 \text{mAdc}$) ($I_F = 150 \text{mAdc}$)	V_F	-	-	715 855 1000 1250	mV_{dc}

Typical Characteristic Curves

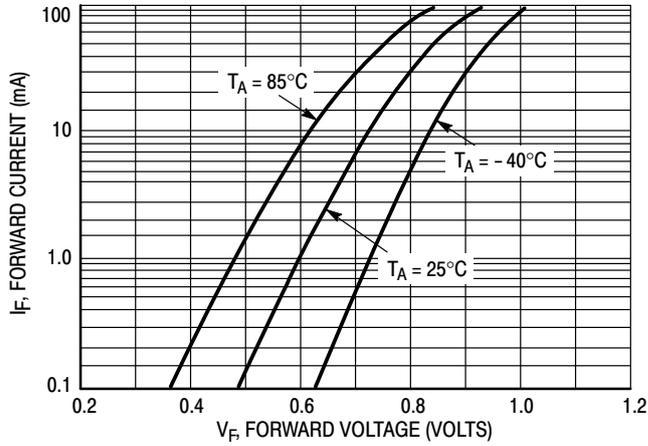


Figure 1. Forward Voltage

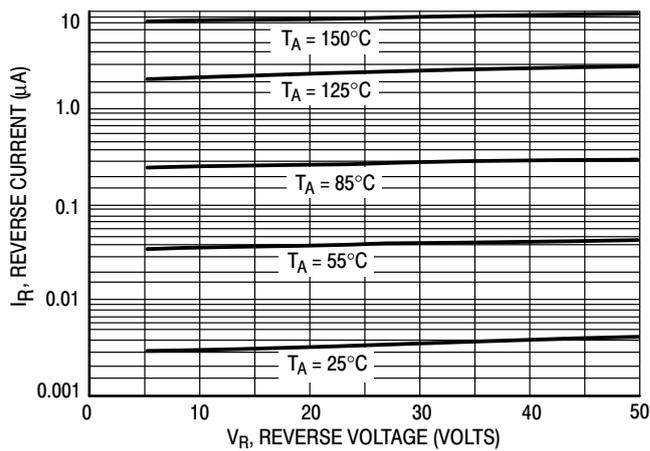


Figure 2. Leakage Current

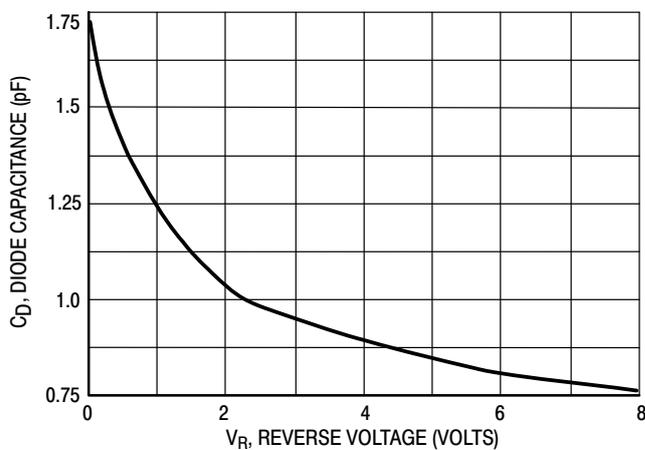
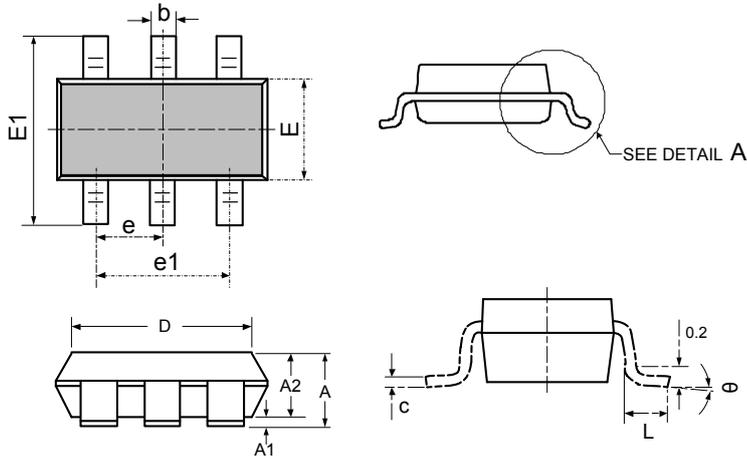


Figure 3. Capacitance

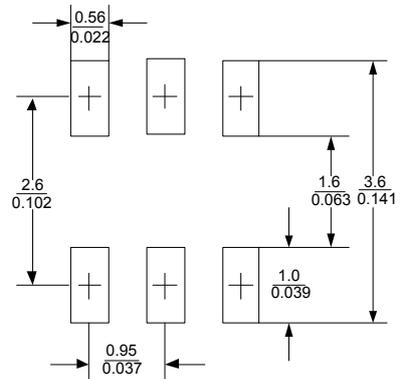
Outline Drawing – SOT23-6



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	0.041	0.049	1.050	1.250
A1	0.000	0.004	0.000	0.100
A2	0.041	0.045	1.050	1.150
D	0.111	0.119	2.820	3.020
E	0.059	0.067	1.500	1.700
E1	0.104	0.116	2.650	2.950
b	0.012	0.020	0.300	0.500
e	0.037(BSC)		0.950(BSC)	
e1	0.071	0.079	1.800	2.000
L	0.012	0.024	0.300	0.600
θ	0°	8°	0°	8°

Notes

- This land pattern is for reference purposes only consult your manufacturing group to ensure your company's manufacturing guidelines are met.



Marking



Ordering information

Order code	Package	Base qty	Delivery mode
NUP4301MR6	SOT23-6	3k	Tape and reel

CCS Semiconductor and are trademarks of Semiconductor Components Industries, CCS Semiconductor reserves the right to make changes without further notice to any products herein. CCS Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does CCS Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. CCS Semiconductor does not convey any license under its patent rights nor the rights of others.